

Deyildiz

List of Publications by Year in descending order

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62
papers

1,384
citations

377584

21
h-index

425179

34
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63
all docs

63
docs citations

63
times ranked

1200
citing authors

#	ARTICLE	IF	CITATIONS
1	Selenophene-containing conjugated polymers for supercapacitor electrodes. <i>Journal of Polymer Science</i> , 2022, 60, 109-121.	2.0	6
2	Effect of illumination on electrical characteristics of Au/Mn-complex/n-Si photodiode structures. <i>Journal of Materials Science: Materials in Electronics</i> , 2022, 33, 2631-2642.	1.1	7
3	Effect of TiO ₂ Thin Film with Different Dopants in Bringing Au-Metal into a Contact with n-Si. <i>Journal of Inorganic and Organometallic Polymers and Materials</i> , 2022, 32, 1067-1077.	1.9	5
4	Synthesize and characterization of Co-complex as interlayer for Schottky type photodiode. <i>Polymer Bulletin</i> , 2022, 79, 11389-11408.	1.7	13
5	Si-based photosensitive diode with novel Zn-doped nicotinate/nicotinamide mixed complex interlayer. <i>Materials Science in Semiconductor Processing</i> , 2022, 147, 106750.	1.9	5
6	Dark and illuminated electrical characteristics of Schottky device with Zn-complex interface layer. <i>Journal of Materials Science: Materials in Electronics</i> , 2022, 33, 18039-18053.	1.1	7
7	Dielectric characterization of Al/PCBM:ZnO/p-Si structures for wide-range frequency. <i>Bulletin of Materials Science</i> , 2021, 44, 1.	0.8	6
8	Effect of atomic-layer-deposited HfO ₂ thin-film interfacial layer on the electrical properties of Au/Ti/n-GaAs Schottky diode. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 10209-10223.	1.1	20
9	Capacitance, conductance, and dielectric characteristics of Al/TiO ₂ /Si diode. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 13549-13567.	1.1	14
10	A study on electrical properties of Au/4H-SiC Schottky diode under illumination. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 20130-20138.	1.1	7
11	Analysis of Double Gaussian Distribution on Barrier Inhomogeneity in a Au/n-4H SiC Schottky Diode. <i>Journal of Electronic Materials</i> , 2021, 50, 7044-7056.	1.0	5
12	Dark and illuminated electrical characteristics of Si-based photodiode interlayered with CuCo ₅ S ₈ nanocrystals. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 935-948.	1.1	24
13	Electrical characteristics of organic heterojunction with an alternating benzotriazole and fluorene containing copolymer. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 18816-18831.	1.1	12
14	Electrical characterization of CdZnTe/Si diode structure. <i>Applied Physics A: Materials Science and Processing</i> , 2020, 126, 1.	1.1	9
15	Analysis of temperature-dependent forward and leakage conduction mechanisms in organic thin film heterojunction diode with fluorine-based PCBM blend. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 15233-15242.	1.1	9
16	The dielectric performance of Au/CuCo ₅ S ₈ /p-Si heterojunction for various frequencies. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 22408-22416.	1.1	13
17	Frequency effect on electrical and dielectric characteristics of HfO ₂ -interlayered Si-based Schottky barrier diode. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 9394-9407.	1.1	21
18	Electrical properties of Al/PCBM:ZnO/p-Si heterojunction for photodiode application. <i>Journal of Alloys and Compounds</i> , 2020, 827, 154279.	2.8	61

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19	Electrical characteristics of atomic layer deposited Au/Ti/HfO ₂ /n-GaAs MIS diodes in the wide temperature range. Journal of Materials Science: Materials in Electronics, 2020, 31, 7839-7849.	1.1	30
20	Temperature and frequency effects on electrical and dielectric properties of n-4H SiC based metal-insulator-semiconductor (MIS) diode interlayered with Si ₃ N ₄ thin film. Journal of Materials Science: Materials in Electronics, 2020, 31, 8705-8717.	1.1	23
21	Investigation of electrical characteristics of Ag/ZnO/Si sandwich structure. Journal of Materials Science: Materials in Electronics, 2019, 30, 15371-15378.	1.1	12
22	Analysis of forward and reverse biased current-voltage characteristics of Al/Al ₂ O ₃ /n-Si Schottky diode with atomic layer deposited Al ₂ O ₃ thin film interlayer. Journal of Materials Science: Materials in Electronics, 2019, 30, 19383-19393.	1.1	27
23	Determination of current transport characteristics in Au-Cu/CuO/n-Si Schottky diodes. Physica B: Condensed Matter, 2019, 570, 246-253.	1.3	20
24	Frequency effect on electrical and dielectric characteristics of In/Cu ₂ ZnSnTe ₄ /Si/Ag diode structure. Journal of Materials Science: Materials in Electronics, 2019, 30, 9814-9821.	1.1	11
25	Temperature dependence of electrical properties in In/Cu ₂ ZnSnTe ₄ /Si/Ag diodes. Bulletin of Materials Science, 2019, 42, 1.	0.8	13
26	Analysis of current conduction mechanism in CZTSSe/n-Si structure. Journal of Materials Science: Materials in Electronics, 2018, 29, 5264-5274.	1.1	20
27	Investigation of carrier transport mechanisms in the Cu-Zn-Se based hetero-structure grown by sputtering technique. Canadian Journal of Physics, 2018, 96, 816-825.	0.4	10
28	Temperature-Dependent Electrical Characteristics of Au/Si ₃ N ₄ /4H n-SiC MIS Diode. Journal of Electronic Materials, 2018, 47, 2979-2987.	1.0	24
29	Electrical properties of Au-Cu/ZnO/p-Si diode fabricated by atomic layer deposition. Journal of Materials Science: Materials in Electronics, 2018, 29, 17802-17808.	1.1	23
30	Influence of Si ₃ N ₄ layer on the electrical properties of Au/n-4H SiC diodes. Bulletin of Materials Science, 2018, 41, 1.	0.8	5
31	Effect of layer thickness on the electrical parameters and conduction mechanisms of conjugated polymer-based heterojunction diode. Journal of Applied Polymer Science, 2017, 134, .	1.3	16
32	A triazoloquinoxaline and benzodithiophene bearing low band gap copolymer for electrochromic and organic photovoltaic applications. Synthetic Metals, 2017, 228, 111-119.	2.1	13
33	Benzodithiophene and Benzotriazole Bearing Conjugated Polymers for Electrochromic and Organic Solar Cell Applications. Journal of the Electrochemical Society, 2017, 164, G71-G76.	1.3	13
34	ELECTRICAL PROPERTIES OF Al/p-Si STRUCTURE WITH Al ₂ O ₃ THIN FILM FABRICATED BY ATOMIC LAYER DEPOSITION SYSTEM. Surface Review and Letters, 2017, 24, 1750077.	0.5	2
35	Study on the electrical properties of ZnSe/Si heterojunction diode. Journal of Materials Science: Materials in Electronics, 2017, 28, 17806-17815.	1.1	26
36	Study on the Reverse Bias Carrier Transport Mechanism in Au/TiO ₂ /n-4H-SiC Structure. Journal of Nanoelectronics and Optoelectronics, 2016, 11, 626-630.	0.1	6

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37	The effect of ultraviolet irradiation on the ultra-thin HfO ₂ based CO gas sensor. Journal of Applied Physics, 2015, 118, .	1.1	16
38	Frequency and voltage dependence of electric and dielectric properties of Au/TiO ₂ /n-4H-SiC (metal-insulator-semiconductor) type Schottky barrier diodes. Physica Scripta, 2015, 90, 095801.	1.2	40
39	On the negative capacitance behavior in the forward bias of Au/HfO ₂ /SiC (MS) and comparison between MS and Au/TiO ₂ /HfO ₂ /SiC (MIS) type diodes both in dark and under 200 W illumination intensity. International Journal of Modern Physics B, 2015, 29, 1450237.	1.0	17
40	Synthesis of a benzotriazole bearing alternating copolymer for organic photovoltaic applications. New Journal of Chemistry, 2015, 39, 6623-6630.	1.4	19
41	Silafluorene-based polymers for electrochromic and polymer solar cell applications. Journal of Polymer Science Part A, 2015, 53, 1541-1547.	2.5	24
42	CO ₂ gas detection properties of a TiO ₂ /Al ₂ O ₃ heterostructure under UV light irradiation. Physica Scripta, 2015, 90, 055802.	1.2	39
43	Benzotriazole and benzodithiophene containing medium band gap polymer for bulk heterojunction polymer solar cell applications. Journal of Polymer Science Part A, 2015, 53, 528-535.	2.5	20
44	ALD TiO ₂ thin film as dielectric for Al/p-Si Schottky diode. Bulletin of Materials Science, 2014, 37, 1563-1568.	0.8	32
45	Analysis of temperature dependent current-conduction mechanisms in Au/TiO ₂ /n-4H-SiC (metal/insulator/semiconductor) type Schottky barrier diodes. Journal of Applied Physics, 2014, 116, .	1.1	68
46	Investigation on dielectric properties of atomic layer deposited Al ₂ O ₃ dielectric films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	0.9	14
47	Leakage current by Frenkel-Poole emission on benzotriazole and benzothiadiazole based organic devices. Materials Science in Semiconductor Processing, 2014, 28, 84-88.	1.9	16
48	UV light activated gas sensor for NO ₂ detection. Materials Science in Semiconductor Processing, 2014, 28, 43-47.	1.9	41
49	Dielectric and electrical properties of an organic device containing benzotriazole and fluorene bearing copolymer. Journal of Applied Polymer Science, 2013, 128, 1659-1664.	1.3	7
50	Optimizing the organic solar cell efficiency: Role of the active layer thickness. Solar Energy Materials and Solar Cells, 2013, 113, 100-105.	3.0	65
51	The Main Electrical and Interfacial Properties of Benzotriazole and Fluorene Based Organic Devices. Journal of Macromolecular Science - Pure and Applied Chemistry, 2013, 50, 168-174.	1.2	13
52	Solution processable benzotriazole and fluorene containing copolymers for photovoltaic applications. Solar Energy Materials and Solar Cells, 2012, 99, 321-326.	3.0	33
53	Benzotriazole and benzothiadiazole containing conjugated copolymers for organic solar cell applications. Polymer, 2012, 53, 1198-1202.	1.8	23
54	Illumination intensity effects on the dielectric properties of schottky devices with Co, Ni-doped PVA nanofibers as an interfacial layer. Advances in Polymer Technology, 2012, 31, 63-70.	0.8	18

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55	Frequency and gate voltage effects on the dielectric properties and electrical conductivity of Al/SiO ₂ /p-Si metal-insulator-semiconductor Schottky diodes. Journal of Applied Physics, 2011, 110, 14507-145075.	1.1	59
56	The effects of surface states and series resistance on the performance of Au/SnO ₂ /n-Si and Al/SnO ₂ /p-Si (MIS) Schottky barrier diodes. Materials Science in Semiconductor Processing, 2010, 13, 34-40.	1.9	23
57	On the temperature dependence of series resistance and interface states in Al/SiO ₂ /p-Si (MIS) Schottky diodes. Microelectronic Engineering, 2008, 85, 289-294.	1.1	21
58	Gaussian distribution of inhomogeneous barrier height in Al/SiO ₂ /p-Si Schottky diodes. Journal of Applied Physics, 2008, 103, .	1.1	73
59	Temperature dependence of characteristic parameters of the Au/SnO ₂ /n-Si (MIS) Schottky diodes. Solid-State Electronics, 2007, 51, 941-949.	0.8	101
60	Current conduction mechanism in Al/p-Si Schottky barrier diodes with native insulator layer at low temperatures. Applied Surface Science, 2007, 253, 5056-5061.	3.1	64
61	The Analysis of Inhomogeneous Barrier Height in In/SnTe/Si/Ag Diode. Journal of Polytechnic, 0, , .	0.4	0
62	Frequency Dependent Dielectric Properties of ZnSe/p-Si Diode. Journal of Polytechnic, 0, , .	0.4	0